DMN2100UDM
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

## Features

- Low On-Resistance
- $55 \mathrm{~m} \Omega @ \mathrm{~V}_{\mathrm{Gs}}=4.5 \mathrm{~V}$
- $70 \mathrm{~m} \Omega @ \mathrm{~V}_{\mathrm{Gs}}=2.5 \mathrm{~V}$
- $90 \mathrm{~m} \Omega @ \mathrm{~V}_{\mathrm{GS}}=1.8 \mathrm{~V}$
- $\quad 130 \mathrm{~m} \Omega$ @ $\mathrm{V}_{\mathrm{GS}}=1.5 \mathrm{~V}$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standard for High Reliability


TOP VIEW

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## Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.015 grams (approximate)

SOT-26


Maximum Ratings $@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic | Symbol | Value | Units |
| :--- | :---: | :---: | :---: |
| Drain-Source Voltage | $V_{\text {DSS }}$ | 20 | V |
| Gate-Source Voltage | $\mathrm{V}_{\text {GSS }}$ | $\pm 8$ | V |
| Drain Current (Note 1) | $\mathrm{I}_{\mathrm{D}}$ | 3.3 | A |
| Pulsed Drain Current (Note 1) | $\mathrm{I}_{\mathrm{DM}}$ | 13 | A |

## Thermal Characteristics $@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic | Symbol | Value | Units |
| :--- | :---: | :---: | :---: |
| Total Power Dissipation (Note 1) | $\mathrm{P}_{\mathrm{D}}$ | 900 | mW |
| Thermal Resistance, Junction to Ambient | $\mathrm{R}_{\text {®JA }}$ | 139 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Operating and Storage Temperature Range | $\mathrm{T}_{J,} \mathrm{~T}_{\text {STG }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

## Electrical Characteristics $@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS (Note 4) |  |  |  |  |  |  |
| Drain-Source Breakdown Voltage | $\mathrm{BV}_{\mathrm{DSS}}$ | 20 | - | - | V | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A}$ |
| Zero Gate Voltage Drain Current | Idss | - | - | 1 | $\mu \mathrm{A}$ | $V_{D S}=20 \mathrm{~V}, \mathrm{~V}_{G S}=0 \mathrm{~V}$ |
| Gate-Source Leakage | Igss | - | - | $\pm 1$ | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{GS}}= \pm 8 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |
| ON CHARACTERISTICS (Note 4) |  |  |  |  |  |  |
| Gate Threshold Voltage | $\mathrm{V}_{\mathrm{GS}}(\mathrm{th})$ | 0.6 | - | 1.0 | V | $\mathrm{V}_{\mathrm{DS}}=\mathrm{V}_{\mathrm{GS}}, \mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A}$ |
| Static Drain-Source On-Resistance | RDS (ON) | - | $\begin{aligned} & 32 \\ & 43 \\ & 56 \\ & 80 \end{aligned}$ | $\begin{gathered} \hline 55 \\ 70 \\ 90 \\ 130 \end{gathered}$ | $\mathrm{m} \Omega$ | $\mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V}, \mathrm{ID}_{\mathrm{D}}=6 \mathrm{~A}$ |
|  |  |  |  |  |  | $\mathrm{V}_{\mathrm{GS}}=2.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=4.0 \mathrm{~A}$ |
|  |  |  |  |  |  | $\mathrm{V}_{\mathrm{GS}}=1.8 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1.5 \mathrm{~A}$ |
|  |  |  |  |  |  | $\mathrm{V}_{\mathrm{GS}}=1.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1.0 \mathrm{~A}$ |
| Forward Transfer Admittance | \|Y fs | | - | 8 | - | S | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=6 \mathrm{~A}$ |
| Diode Forward Voltage (Note 4) | $\mathrm{V}_{\text {SD }}$ | - | 0.7 | 1.1 | V | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{IS}=2 \mathrm{~A}$ |
| DYNAMIC CHARACTERISTICS |  |  |  |  |  |  |
| Input Capacitance | $\mathrm{C}_{\text {iss }}$ | - | 555 | - | pF | $\begin{aligned} & V_{D S}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V} \\ & \mathrm{f}=1.0 \mathrm{MHz} \end{aligned}$ |
| Output Capacitance | $\mathrm{C}_{\text {oss }}$ | - | 112 | - | pF |  |
| Reverse Transfer Capacitance | $\mathrm{C}_{\text {rss }}$ | - | 84 | - | pF |  |

Notes: 1. Device mounted on FR-4 PCB, or minimum recommended pad layout with 2oz. copper pads
2. No purposefully added lead
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead free/index.php.
4. Short duration pulse test used to minimize self-heating effect.


Fig. 3 On-Resistance vs. Drain Current \& Gate Voltage


Fig. 5 Gate Threshold Variation vs. Ambient Temperature


Fig. 2 Typical Transfer Characteristics


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature


Fig. 6 Typical Total Capacitance


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage
Ordering Information (Note 5)

| Part Number | Case | Packaging |
| :---: | :---: | :---: |
| DMN2100UDM-7 | SOT-26 | 3000/Tape \& Reel |

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## Marking Information



## Package Outline Dimensions



| SOT-26 |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
| Dim | Min | Max | Typ |  |
| A | 0.35 | 0.50 | 0.38 |  |
| B | 1.50 | 1.70 | 1.60 |  |
| C | 2.70 | 3.00 | 2.80 |  |
| D | - | - | 0.95 |  |
| H | 2.90 | 3.10 | 3.00 |  |
| J | 0.013 | 0.10 | 0.05 |  |
| K | 1.00 | 1.30 | 1.10 |  |
| L | 0.35 | 0.55 | 0.40 |  |
| M | 0.10 | 0.20 | 0.15 |  |
| $\alpha$ | $0^{\circ}$ | $8^{\circ}$ | - |  |
| All Dimensions in | $\mathbf{m m}$ |  |  |  |
|  |  |  |  |  |

## Suggested Pad Layout



| Dimensions | Value (in mm) |
| :---: | :---: |
| $\mathbf{Z}$ | 3.20 |
| $\mathbf{G}$ | 1.60 |
| $\mathbf{X}$ | 0.55 |
| $\mathbf{Y}$ | 0.80 |
| $\mathbf{C 1}$ | 2.40 |
| $\mathbf{C} 2$ | 0.95 |

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